

BSS84

P-Channel Enhancement Mode Field Effect Transistor -50V, -0.13A, 10Ω

Product Overview

For complete documentation, see the data sheet.

This P-channel enhancement-mode MOSFET is produced using proprietary, high cell density, DMOS technology. This very high density process minimizes on-state resistance and to provide rugged and reliable performance and fast switching. The BSS84 can be used, with a minimum of effort, in most applications requiring up to 0.13 A DC and can deliver current up to 0.52 A. This product is particularly suited to low-voltage applications requiring a low-current high-side switch.

Features

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- Voltage-controlled P-channel small signal switch
- High-Density Cell Design for Low RDS(ON)
- High Saturation Current.

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Status	Compliance	Channel Polarity	Silicon Family	Package Name	Type	Gate Level	Wide SOA Mosfets	Configuration	OPN Consider Technology	$V_{(BR)DSM}$ (V)	$R_{DS(on)Max@V_{GS}=10V(mΩ)}$	V_{GSMax} (V)	$V_{GS(th)Max}$ (V)	I_{dMax} (A)	P_{Max} (W)	$R_{DS(on)Max@V_{GS}=2.5V(mΩ)}$	$R_{DS(on)Max@V_{GS}=4.5V(mΩ)}$	$Q_{typ@V_{GS}=4.5V(nC)}$	$Q_{typ@V_{GS}=10V(nC)}$	$C_{iss}(pF)$	$Q_{typ@V_{GS}=4.5V(nC)}$	$Q_{rr}(pF)$	$C_{oss}(pF)$	$C_{rss}(pF)$	Package Type	Case Outline	MSL Temp (°C)	MSL Type	Container Type	Container Qty.
BSS84	Active		P-Channel	PowerTrench® T1	SOT-23	Small Signal	Logic	0	Single	0	-50	-	±20	-2	-0.13	0.36	-	10000	-	0.9	73	0.3	-	10	5	SOT-23 (TO-236)	318-PDF	1	260	REEL	3000